

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listing of claims in the application.

1-6. (Canceled)

7. (Original) A slurry for use in removing silicon dioxide in preference to silicon nitride by chemical mechanical polishing in the shallow trench isolation process, the slurry comprising:

an aqueous medium having abrasive particles dispersed therein;

and

proline;

wherein the slurry has a pH within the range of from about 6 to about 11 and provides a silicon dioxide to silicon nitride removal rate selectivity of greater than 5:1.

8. (Original) The slurry according to claim 7 wherein the abrasive particles are selected from the group consisting of ceria and titania.

9. (Original) A slurry for use in removing silicon dioxide in preference to silicon nitride by chemical mechanical polishing in the shallow trench isolation process, the slurry comprising:

an aqueous medium having abrasive particles dispersed therein;

and

glycine;

wherein the slurry has a pH within the range of from about 6 to about 11 and provides a silicon dioxide to silicon nitride removal rate selectivity of greater than 5:1.

10. (Original) The slurry according to claim 9 wherein the abrasive particles are selected from the group consisting of ceria and titania.

11. (Original) A slurry for use in removing silicon dioxide in preference to silicon nitride by chemical mechanical polishing in the shallow trench isolation process, the slurry comprising:

an aqueous medium having abrasive particles dispersed therein;

and

alanine;

wherein the slurry has a pH within the range of from about 6 to about 11 and provides a silicon dioxide to silicon nitride removal rate selectivity of greater than 5:1.

12. (Original) The slurry according to claim 11 wherein the abrasive particles are selected from the group consisting of ceria and titania.